

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application:

1. (Currently Amended) An etching method for etching an etching target film formed on an SiO₂ film placed inside an airtight processing chamber, the method comprising:

introducing a processing gas into said airtight processing chamber, wherein said processing gas contains N₂ and at least one of C₄F₈ and CF₄; ~~and~~

generating a plasma in said airtight processing chamber for etching said etching target film, and

etching an organic target film containing Si formed on the SiO₂ film until the SiO₂ film is exposed ~~wherein said etching target film is an organic film containing Si formed on said SiO₂ film, wherein a resist is used as a mask on said etching target film, and wherein said etching target film is etched until said SiO₂ film is exposed.~~

2. (Currently Amended) An etching method according to claim 1, wherein~~[[:]]~~ said organic film containing Si is constituted of SiO₂ containing C and H.

3. (Currently Amended) An etching method according to claim 1, wherein~~[[:]]~~ the dielectric constant of said organic film containing Si is equal to or lower than 3.0.

4. (Currently Amended) An etching method according to claim 1, wherein~~[[:]]~~ said organic target film containing Si is an organic polysiloxane film.

5. (Currently Amended) An etching method according to claim 1, wherein
said processing gas further contains Ar.

Claims 6-13 (Canceled).

14. (Currently Amended) An etching method for etching an etching target film formed on an SiO₂ film placed inside an airtight processing chamber, the method comprising:
introducing a processing gas into said airtight processing chamber, wherein said processing gas contains at least CF₄ and N₂, wherein the flow rate ratio of CF₄ and N₂ in said processing gas is essentially set within a range of $1 \leq (\text{N}_2 \text{ flow rate} / \text{CF}_4 \text{ flow rate}) \leq 4$; and

generating a plasma in said airtight processing chamber for etching said etching target film, and

etching an organic target film containing Si formed on the SiO₂ film until the SiO₂ film is exposed ~~wherein said etching target film is an organic film containing Si formed on said SiO₂ film, wherein a resist is used as a mask on said etching target film, and wherein said etching target film is etched until said SiO₂ film is exposed.~~

Claims 15 -17 (Canceled).